MR501, MR502, MR504 MR506, MR508, MR510

Designers Data Sheet

MINIATURE SIZE, AXIAL LEAD MOUNTED STANDARD RECOVERY POWER RECTIFIERS

 \ldots , designed for use in power supplies and other applications having need of a device with the following features:

- High Current to Small Size
- High Surge Current Capability
- Low Forward Voltage Drop
- Void-Free Economical Plastic Package
- Available in Volume Quantities

Designer's Data for "Worst Case" Conditions

The Designers Data sheets permit the design of most circuits entirely from the information presented. Limit curves — representing boundaries on device characteristics — are given to facilitate "worst case" design.

MAXIMUM RATINGS

Rating	Symbol	MR 501	MR 502	MR 504	MR 506	MR 508	MR 510	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	VRRM VRWM VR	100	200	400	600	800	1000	Volts
Non-Repetitive Peak Reverse Voltage	V _{RSM}	150	250	450	650	850	1050	Volts
Average Rectified Forward Current (Single phase resistive load, T _A = 95°C, PC Board Mounting) (1) (EIA Standard Conditions L = 1/32", T _L = 85°C)	ō	3.0				Amp		
Non-Repetitive Peak Surge Current (surge applied at rated load conditions)	IFSM	(one cycle)				Amp		
Operating and Storage Junction Temperature Range (2)	TJ,Tstg			-65 to	+175		-	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	R _θ JA	28	°C/W
(Recommended Printed Circuit Board	1		ŀ
Mounting, See Note 2 on Page 4).	1		i

ELECTRICAL CHARACTERISTICS

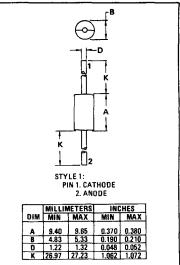
Symbol	Min	Тур	Max	Unit
VE				Volts
1 ' 1	_	0.9	1.0	
]	-	1.04	1.1	
I _R				μА
	_	0.1	5.0	
l l	_	2.8	25	
	٧F	VF	VF - 0.9 - 1.04	VF - 0.9 1.0 - 1.04 1.1

- (1) Derate for reverse power dissipation. Sea Note on Page 2.
- (2) Derate as shown in Figure 1.
- (3) Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2.0%.

STANDARD RECOVERY POWER RECTIFIERS

100-1000 VOLTS 3 AMPERE





CASE 267-01

MECHANICAL CHARACTERISTICS

Case: Void Free, Transfer Molded Finish: External Leads are Plated, Leads are readily Solderable Polarity: Indicated by Cathode Band Weight: 1.1 Grams (Approximately) Maximum Lead Temperature for Soldering Purposes:

300°C, 1/8" from case for 10 s

at 5.0 lb. tension

NOTE 1: DETERMINING MAXIMUM RATINGS

Reverse power dissipation and the possibility of thermal runaway must be considered when operating this rectifier at reverse voltages above 200 volts. Proper derating may be accomplished by use of equation (1):

$$T_{A(mex)} = T_{J(mex)} - R_{\theta JA}P_{F(AV)} - R_{\theta JA}P_{R(AV)}$$
 (1)

TA(max) = Maximum allowable ambient temperature

T_J(max) = Maximum allowable junction temperature (175°C or the temperature at which thermal runaway occurs, whichever is lowest.)

PF(AV) * Average forward power dissipation

PR(AV) = Average reverse power dissipation

 $R_{\theta JA}$ = Junction-to-ambient thermal resistance

Figure 1 permits easier use of equation (1) by taking reverse power dissipation and thermal runaway into consideration. The figure solves for a reference temperature as determined by equation (2):

$$T_{R} = T_{J(max)} - R_{\theta JA} P_{R(AV)}$$
 (2)

Substituting equation (2) into equation (1) yields:

$$T_{A(max)} = T_{R} - R_{\theta J} A^{P} F(AV)$$
 (3)

Inspection of equations (2) and (3) reveals that T_R is the ambient temperature at which thermal runaway occurs or where $T_J=175^{\circ}C$,

when forward power is zero. The transition from one boundary condition to the other is evident on the curves of Figure 1 as a difference in the rate of change of the slope in the vicinity of 165°C. The data of Figure 1 is based upon dc conditions. For use in common rectifier circuits, Table 1 indicates suggested factors for an equivalent dc voltage to use for conservative design; i.e.:

$$V_{R(equiv)} = V_{in}(PK) \times F$$
 (4)

The Factor F is derived by considering the properties of the various rectifier circuits and the rectifiers reverse characteristics.

Exemple: Find $T_{A(max)}$ for MR510 operated in a 400 Volt de supply using a full wave center-tapped circuit with capacitive filter such that $1_{DC} = 6.0$ A, $(1_{F(AV)} = 3.0$ A), $1_{(PK)}/1_{(AV)} = 10$, Input Voltage = 283 V(rms) (line to center tap), $R_{B/A} = 28^{\circ}C/M$.

Step 2: Find
$$T_R$$
 from Figure 1. Read T_R = 167°C @ $V_R \approx 444 \ V \& R_{\theta JA} = 28^{\circ} C/W$.

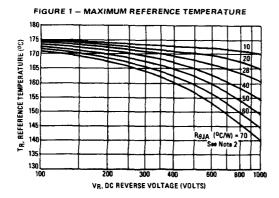
Step 4: Find
$$T_{A(max)}$$
 from equation (3). $T_{A(max)} = 167-(28)$
(4) = 55 °C.

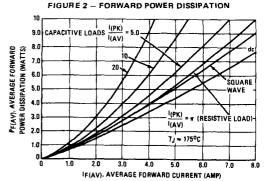
TABLE I - VALUES FOR FACTOR F

Circuit	Half	Wave	Full Wav	re, Bridge	Full Wave Center-Tapped*†		
Load Resist	Resistive	Capacitive*	Resistive	Capacitive	Resistive	Capacitive	
Sine Wave	0.45	1.11	0.45	0.55	0.90	1.11	
Square Wave	0.61	1.22	0.61	0.61	1.22	1.22	

^{*}Note that VR(PK) ≈ 2 Vin(PK)

[†]Use line to center tap voltage for Vin-







(Reverse Power Loss Neglected)

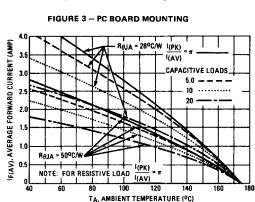


FIGURE 4 - SEVERAL LEAD LENGTHS

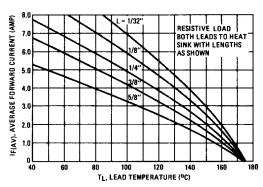


FIGURE 5 - 1/8" LEAD LENGTH

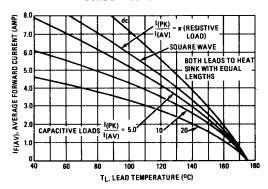


FIGURE 6 - FORWARD VOLTAGE

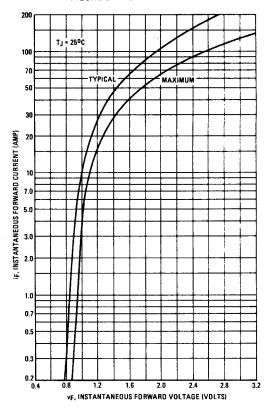
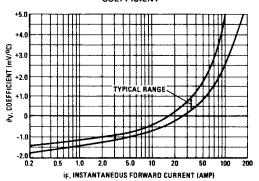
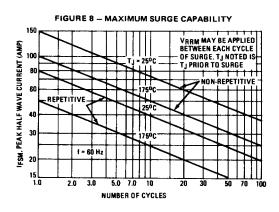
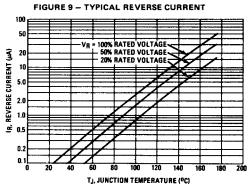


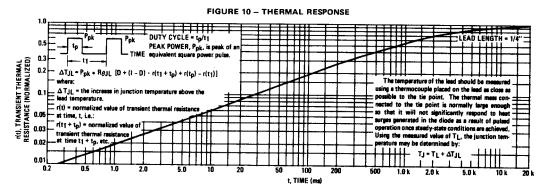
FIGURE 7 – FORWARD VOLTAGE TEMPERATURE COEFFICIENT

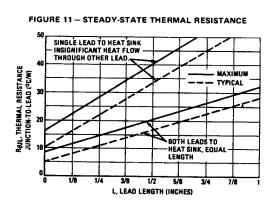






THERMAL CHARACTERISTICS





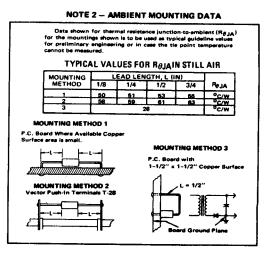
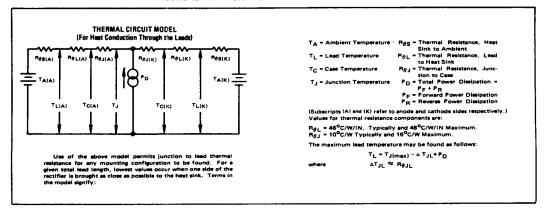
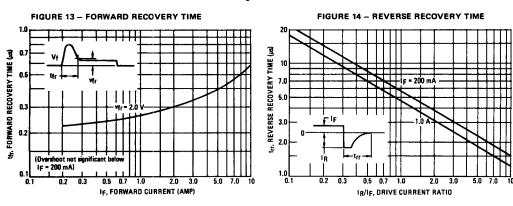


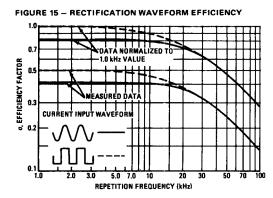
FIGURE 12 - APPROXIMATE THERMAL CIRCUIT MODEL

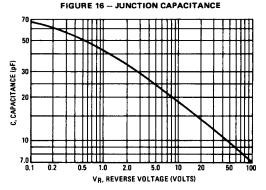


TYPICAL DYNAMIC CHARACTERISTICS

 $(T_J = 25^{\circ}C)$

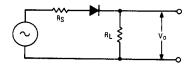






RECTIFIER EFFICIENCY NOTE

FIGURE 17 — SINGLE-PHASE HALF-WAVE RECTIFIER CIRCUIT



The rectification efficiency factor σ shown in Figure 15 was calculated using the formula:

$$\sigma = \frac{\frac{P(dc)}{P_{(rms)}}}{\frac{P(dr)}{V_{o}(rms)}} = \frac{\frac{V_{o}^{2}(dc)}{R_{L}}}{\frac{V_{o}^{2}(rms)}{R_{L}}} \cdot 100\% = \frac{V_{o}^{2}(dc)}{V_{o}^{2}(ac) + V_{o}^{2}(dc)} \cdot 100\% (1)$$

For a sine wave input $\,V_{m}\,$ sin $\,(\omega t)\,$ to the diode, assumed lossless, the maximum theoretical efficiency factor becomes:

$$\sigma_{\text{(sine)}} = \frac{\frac{V_{\text{m}}^2}{\pi^2 R_{\text{L}}}}{\frac{V_{\text{m}}^2}{4R_{\text{L}}}} \cdot 100\% = \frac{4}{\pi^2} \cdot 100\% = 40.6\%$$
 (2)

For a square wave input of amplitude V_m, the efficiency factor becomes:

$$\sigma(\text{square}) = \frac{\frac{V^2 \text{m}}{2R_L}}{\frac{V^2 \text{m}}{R_L}} \cdot 100\% = 50\% (3)$$

(A full wave circuit has twice these efficiencies)

As the frequency of the input signal is increased, the reverse recovery time of the diode (Figure 14) becomes significant, resulting in an increasing as voltage component across R_{\perp} which is opposite in polarity to the forward current, thereby reducing the value of the efficiency factor $\sigma_{\rm c}$ as shown on Figure 15.

It should be emphasized that Figure 15 shows waveform efficiency only; it does not provide a measure of diode losses. Data was obtained by measuring the ac component of V_0 with a true rms ac voltmeter and the dc component with a dc voltmeter. The data was used in Equation 1 to obtain points for the figure.